

SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY:: PUTTUR
(AUTONOMOUS)

B.Tech III Year I Semester Supplementary Examinations June-2024
ELECTRONIC DEVICES AND CIRCUITS
(Electronics & Communication Engineering)

Time: 3 Hours**Max. Marks: 60**

(Answer all Five Units 5 x 12 = 60 Marks)

UNIT-I

1 a Elaborate the action of PN junction diode under forward bias and reverse bias and sketch its V-I Characteristics. CO1 L6 6M

b List the applications of PN junction and Zener diodes. CO1 L1 6M

OR

2 a Draw and explain the V-I characteristics of Zener diode CO1 L2 6M

b Show that the Zener diode can act as a voltage regulator with a neat diagram. CO1 L1 6M

UNIT-II

3 a Draw the circuit diagram of a Full wave rectifier and with the help of waveforms describe its operation. CO1 L1 6M

b A full wave rectifier circuit is fed from a transformer having a center-tapped secondary winding. The rms voltage from either end of secondary to center tap is 30V. If the diode forward resistance is 2Ω and that of the half secondary is 8Ω , for a load of $1\text{ K}\Omega$. Solve DC power delivered to the load, efficiency of rectification. CO2 L3 6M

OR

4 a Explain the working and characteristics of SCR in Forward and Reverse Blocking Mode. CO1 L2 6M

b Explain working principle and characteristics of LED with neat diagram. Also list the applications of LED. CO2 L2 6M

UNIT-III

5 a Explain the Input and Output characteristics of a BJT in CE Configuration. Indicate the regions of operations in the output characteristics and list the applications in those regions. CO5 L2 6M

b Define α , β and γ of a Transistor and Evaluate the relation between them. CO1 L5 6M

OR

6 a With the help of neat diagram, Explain the operation and characteristics of n-channel enhancement type MOSFET. CO5 L2 6M

b List difference between depletion and enhancement MOSFET. CO1 L1 6M

UNIT-IV

7 a Estimate the stability factors S , S' and S'' of a BJT Voltage Divider bias. CO6 L5 6M

b Explain the concept of DC and AC Load lines and discuss the criteria for fixing the Q-point. CO3 L2 6M

OR

8 a Explain Thermal Runaway and Thermal Resistance. CO3 L2 6M

b Explain Sensistor Compensation Technique. CO3 L2 6M

UNIT-V

9 a Discuss about the frequency response of an amplifier. CO1 L6 6M

b Determine the parameters A_i , R_i , A_v and R_o of Common Collector Amplifier using simplified hybrid model analysis. CO3 L5 6M

OR

- 10 a Develop the expression for current gain, voltage gain, input impedance and output impedance for Common Emitter Amplifier with Emitter Resistor using simplified hybrid model. C03 L3 6M
- b A CE amplifier is driven by a voltage source of internal resistance $R_s = 1000\Omega$ and the load impedance of $R_C = 2k\Omega$. The h-parameters are $h_{ie} = 1.3k$, $h_{fe} = 55$, $h_{oe} = 22\mu A/V$ and $h_{re} = 2 \times 10^{-4}$. Neglecting biasing resistors, Estimate the value of current gain, voltage gain, input impedance, output impedance for the value of Emitter Resistor $R_E = 200\Omega$ inserted in the emitter circuit. C02 L5 6M

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